



TO-92 Plastic-Encapsulate Transistors (PNP)

A1015

A1015 TRANSISTOR (PNP)

FEATURES

Power dissipation

$$P_{CM}: 0.4 \text{ W (Tamb=25°C)}$$

Collector current

$$I_{CM}: -0.15 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO}: -50 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg}: -55°C \text{ to } +150°C$$

TO-92

1. EMITTER

2. COLLECTOR

3. BASE



ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu A, I_E = 0$	-50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -0.1 \text{ mA}, I_B = 0$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu A, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -50 \text{ V}, I_E = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5 \text{ V}, I_C = 0$			-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -6 \text{ V}, I_C = -2 \text{ mA}$	70		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100 \text{ mA}, I_B = -10 \text{ mA}$			-0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -100 \text{ mA}, I_B = -10 \text{ mA}$			-1.1	V
Transition frequency	f_T	$V_{CE} = -10 \text{ V}, I_C = -1 \text{ mA}$ $f = 30 \text{ MHz}$	80			MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	O	Y	GR
Range	70-140	120-240	200-400